

**AMENDED CLAIMS**

[received by the International Bureau on 20 June 2005 (20.06.05);  
original claims 1-28 replaced by new claims 1-30 (7 pages)]

- 10 1. A device (101) for regulating a voltage supply to a semiconductor device (100), said device comprising a memory (103) for storing a plurality of performance ranges, wherein said performance ranges are associated with a respective supply voltage; a measuring function for measuring a performance of said semiconductor device (100); and a regulator (112) wherein the device (101) is characterised in that the memory (103) stores a performance limit of the semiconductor device (100) and a reference circuit (107) is coupled to the memory (103) and is arranged to determine a lowest
- 15 supply voltage required to maintain a performance of the semiconductor device (100) at a given operational frequency and modify the supply voltage to said semiconductor device (100) if a measured performance of said semiconductor device is not within a predetermined portion of said performance range associated with said voltage supplied to said
- 20 semiconductor device (100).
- 25 2. A device (101) according to claim 1, wherein said performance limits stored in the memory (103) are based on two parameters: a current resistance drop value and an accuracy of the regulator (112).
- 30 3. A device (101) according to claim 1, wherein said performance range is defined to have an upper performance limit (201) such that if said measured performance of the semiconductor device (100) is above said upper performance limit (201) said regulator (112) is arranged to reduce said voltage supplied to said semiconductor device (100).

- 5        4. A device according to claim 1, wherein said performance range is defined to have a lower performance limit (202) such that if said measured performance of said semiconductor device (100) is below said lower performance limit (202) said regulator (112) is arranged to increase said voltage supplied to the semiconductor device(100).
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- 15        5. A device according to claim 1, wherein said performance range is defined to have a critical lower performance limit (203) such that if said measured performance of said semiconductor device (100) is below said critical lower performance limit (203) said regulator is arranged to increase said voltage supplied to said semiconductor device.
- 20        6. A device (101) according to claim 1, wherein said measuring function is arranged to measure said performance of said semiconductor device (100) by measuring said performance of a reference circuit (107) that forms part of said semiconductor device (100).
- 25        7. A device (101) according to claim 6, wherein said plurality of performance ranges are arranged to include a performance guard margin to compensate for differences between said measured performance of said reference circuit (107) and an actual performance of a complete integrated circuit (100).
- 30        8. A device (101) according to claim 1, further comprising a ring oscillator (107), wherein said measuring function measures a frequency of said ring oscillator (107) for providing a measure of said performance of an integrated circuit (100).

5 9. A method for regulating a voltage supply to a semiconductor device, said  
method comprising storing a plurality of performance ranges of the  
semiconductor device (100), wherein respective performance ranges are  
associated with a respective supply voltage; measuring a performance of  
said semiconductor device; wherein the method is characterised by the step  
10 of determining a lowest supply voltage required to maintain a performance  
of the semiconductor device (100) at a given operational frequency and  
modifying said supply voltage to said semiconductor device if a measured  
performance of said semiconductor device is not within a predetermined  
portion of a performance range associated with said voltage supplied to  
15 said semiconductor device.

10. A device (101) for regulating a voltage supply to a semiconductor device  
(100) according to claim 1, wherein the memory (103) also stores a plurality  
of process temperature compensation voltage values, wherein said  
20 respective process temperature compensation voltage values are  
associated with a respective operational frequency for said semiconductor  
device (100); such that if said operational frequency of said semiconductor  
device (100) changes to a new operational frequency, said supply voltage is  
modified by said regulator to substantially a same value as said process  
25 temperature compensation voltage value associated with said new  
operation frequency.

11. A device (101) according to claim 10, wherein each process temperature  
compensation voltage value associated with a respective operational  
frequency is determined from a plurality of performance ranges stored in  
30 said memory (103) wherein said respective performance ranges are  
associated with a respective supply voltage.

12. A device (101) according to claim 11, further comprising a measuring  
function for measuring the performance of the semiconductor device (100),  
wherein said regulator (112) is arranged to modify said supply voltage to  
35 said semiconductor device (100) if a measured performance of said

- 5 semiconductor device (100) is not within a predetermined portion of a performance range associated with said voltage supplied to the semiconductor device for a given frequency.
- 10 13.A device (101) according to claim 12, wherein said performance range is defined to have an upper performance limit such that if said measured performance of said semiconductor device (100) is above said upper performance limit said regulator (112) is arranged to reduce said voltage supplied to said semiconductor device (100).
- 15 14.A device (101) according to claim 12, wherein said performance range is defined to have a lower performance limit such that if said measured performance of said semiconductor device (100) is below said lower performance limit said regulator (112) is arranged to increase said voltage supplied to said semiconductor device (100).
- 20 15.A device (101) according to claim 12, wherein said performance range is defined to have a critical lower performance limit such that if said measured performance of said semiconductor device (100) is below said critical lower performance limit said regulator (112) is arranged to increase said voltage supplied to said semiconductor device (100).
- 25 16.A device (101) according to claim 12, wherein said measuring function is arranged to measure the performance of said semiconductor device (100) by measuring said performance of a reference circuit that forms part of said semiconductor device (100).
- 30 17.A device (101) according to claim 16, wherein said plurality of performance ranges are arranged to include a performance guard margin to compensate for differences between said measured performance of said reference circuit and an actual performance of said semiconductor device (100).
- 18.A device (101) according to claim 12, further comprising a ring oscillator, wherein said measuring function measures a frequency of said ring oscillator for providing a measure of a performance of the semiconductor device (100).

5 19.A method for regulating a voltage supply to a semiconductor device,  
according to claim 9 wherein said set of storing comprises storing a plurality  
of process temperature compensation voltage values, wherein respective  
process temperature compensation voltage values are associated with a  
respective operational frequency for said semiconductor device; and said  
10 step of modifying comprises modifying a supply voltage to said  
semiconductor device if an operational frequency of said semiconductor  
device changes to a new operational frequency, wherein said supply  
voltage is modified to substantially a same value as a process temperature  
compensation voltage value associated with said new operational  
15 frequency.

20.A device (101) for regulating a voltage supply to a semiconductor device  
(100), said device comprising a memory (103) for storing a plurality of  
process temperature compensation voltage values, wherein said respective  
process temperature compensation voltage values are associated with a  
20 respective operational frequency for said semiconductor device (100); and a  
regulator (112) for modifying said supply voltage to said semiconductor  
device (100) if said operational frequency of said semiconductor device  
(100) changes to a new operational frequency, and wherein the device  
(101) is characterised in that the memory (103) stores a performance limit  
25 of the semiconductor device (100) and a reference circuit (107) is coupled  
to the memory (103) and is arranged to determine a lowest supply voltage  
required to maintain a performance of the semiconductor device (100) at a  
given operational frequency and modify said supply voltage to substantially  
a same value as said process temperature compensation voltage value  
30 associated with said new operational frequency,

21.A device (101) according to claim 20, wherein said performance limit stored  
in the memory (103) is based on a current resistance drop value and an  
accuracy of the regulator (112).



- 5        22.A device (101) according to claim 20, wherein each process temperature compensation voltage value associated with a respective operational frequency is determined from a plurality of performance ranges stored in said memory (103) wherein said respective performance ranges are associated with a respective supply voltage.
- 10       23.A device (101) according to claim 22, further comprising a measuring function for measuring the performance of the semiconductor device, wherein said regulator (112) is arranged to modify said supply voltage to said semiconductor device (100) if a measured performance of the semiconductor device (100) is not within a predetermined portion of a performance range associated with said voltage supplied to said semiconductor device for a given frequency.
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- 20       24.A device (101) according to claim 23, wherein said performance range is defined to have an upper performance limit such that if said measured performance of said semiconductor device (100) is above said upper performance limit said regulator is arranged to reduce said voltage supplied to said semiconductor device (100).
- 25       25.A device (101) according to claim 23, wherein said performance range is defined to have a lower performance limit such that if said measured performance of said semiconductor device (100) is below said lower performance limit said regulator (112) is arranged to increase said voltage supplied to said semiconductor device (100).
- 30       26.A device (101) according claim 23, wherein said performance range is defined to have a critical lower performance limit such that if the measured performance of said semiconductor device (100) is below said critical lower performance limit said regulator (112) is arranged to increase said voltage supplied to said semiconductor device (100).
- 27.A device (101) according to claim 23, wherein said measuring function is arranged to measure the performance of said semiconductor device by

5           measuring said performance of a reference circuit that forms part of said semiconductor device (100).

28. A device (101) according to claim 27, wherein said plurality of performance ranges are arranged to include a performance guard margin to compensate for differences between said measured performance of said reference  
10           circuit and an actual performance of said semiconductor device.

29. A device (101) according to claim 23, further comprising a ring oscillator, wherein said measuring function measures a frequency of said ring oscillator for providing a measure of a performance of the semiconductor device.

15           30. A method for regulating a voltage supply to a semiconductor device, said method comprising storing a plurality of process temperature compensation voltage values, wherein respective process temperature compensation voltage values are associated with a respective operational frequency for said semiconductor device; and modifying a supply voltage to said  
20           semiconductor device if an operational frequency of said semiconductor device changes to a new operational frequency, wherein the method is characterised by the step of determining a lowest supply voltage required to maintain a performance of the semiconductor device (100) at a given operational frequency and modifying said supply voltage to substantially a  
25           same value as a process temperature compensation voltage value associated with said new operational frequency.

**Statement under Article 19(1) PCT**

**Re: Patent Application PCT/IB2004/003939 in the name of Freescale Semiconductor, Inc**

**Amendments and support therefor:**

Claim 1, Claim 8 (renumbered as Claim 9), Claim 19 (renumbered as Claim 20) and Claim 28 (renumbered as Claim 30) have been amended to include the feature that the memory stores a performance limit of the semiconductor device and a reference circuit is arranged to determine a lowest supply voltage required to maintain a performance of the semiconductor device at a given operational frequency. Support for this feature can be found throughout the Specification as originally filed, not least on page 6, lines 12-23.

New Claims 2 and 21 have been introduced, targeted towards the performance limits stored in the memory being based on a current-resistance drop value and an accuracy of the regulator. Support for this feature can be found at least on page 7, lines 15-24 of the Specification as originally filed.

Subsequent Claims have been re-numbered accordingly.